

54ACTQ/74ACTQ14

Quiet Series Hex Inverter with Schmitt Trigger Input

General Description

The 'ACTQ14 contains six inverter gates each with a Schmitt trigger input. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals. In addition, they have a greater noise margin than conventional inverters.

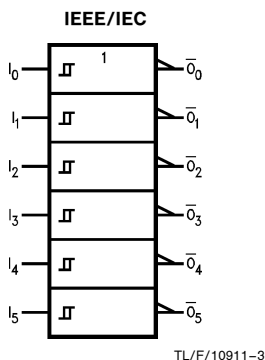
The 'ACTQ14 utilizes NSC Quiet Series Technology to guarantee quiet output switching and improve dynamic threshold performance. FACT Quiet Series™ features GTO™ output control and undershoot corrector in addition to a split ground bus for superior performance.

The 'ACTQ14 has hysteresis between the positive-going and negative-going input thresholds (typically 1.0V) which is determined internally by transistor ratios and is essentially insensitive to temperature and supply voltage variations.

Features

- I_{CC} reduced by 50%
 - Guaranteed simultaneous switching noise level and dynamic threshold performance
 - Improved latch-up immunity
 - 4 kV minimum ESD performance
 - Guaranteed pin-to-pin skew AC performance
 - Outputs source/sink 24 mA
 - Standard Military Drawing (SMD)
- 'ACTQ14: 5962-92183

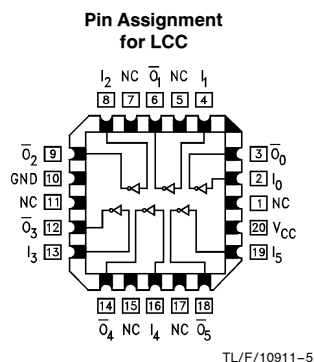
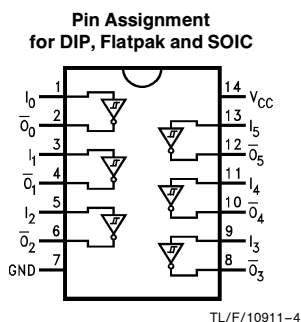
Logic Symbol



Function Table

Input	Output
A	\bar{O}
L	H
H	L

Connection Diagrams



Pin Names	Description
I_n	Inputs
\bar{O}_n	Outputs

Absolute Maximum Rating (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	–0.5V to +7.0V
DC Input Diode Current (I_{IK})	
$V_I = -0.5V$	–20 mA
$V_I = V_{CC} + 0.5V$	+20 mA
DC Input Voltage (V_I)	–0.5V to $V_{CC} + 0.5V$
DC Output Diode Current (I_{OK})	
$V_O = -0.5V$	–20 mA
$V_O = V_{CC} + 0.5V$	+20 mA
DC Output Voltage (V_O)	–0.5V to $V_{CC} + 0.5V$
DC Output Source or Sink Current (I_O)	±50 mA
DC V_{CC} or Ground Current per Output Pin (I_{CC} or I_{GND})	±50 mA
Storage Temperature (T_{STG})	–65°C to +150°C
DC Latch-Up Source or Sink Current	±300 mA
Junction Temperature (T_J)	
CDIP	175°C
PDIP	140°C

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation outside of databook specifications.

Recommended Operating Conditions (Note 2)

Supply Voltage (V_{CC})	4.5V to 5.5V
'ACTQ	
Input Voltage (V_I)	0V to V_{CC}
Output Voltage (V_O)	0V to V_{CC}
Operating Temperature (T_A)	
74ACTQ	–40°C to +85°C
54ACTQ	–55°C to +125°C

Note 2: All commercial packaging is not recommended for applications requiring greater than 2000 temperature cycles from –40°C to +125°C.

DC Characteristics for 'ACTQ Family Devices

Symbol	Parameter	V _{CC} (V)	74ACTQ		54ACTQ		74ACTQ		Units	Conditions
			T _A = +25°C		T _A = −55°C to +125°C		T _A = −40°C to +85°C			
			Typ	Guaranteed Limits						
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0		2.0 2.0		V	V _{OUT} = 0.1V or V _{CC} − 0.1V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8		0.8 0.8		V	V _{OUT} = 0.1V or V _{CC} − 0.1V
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4		4.4 5.4		V	I _{OUT} = −50 μA
		4.5 5.5		3.86 4.86	3.70 4.70		3.76 4.76		V	*V _{IN} = V _{IL} or V _{IH} −24 mA I _{OH} −24 mA
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1		0.1 0.1		V	I _{OUT} = 50 μA
		4.5 5.5		0.36 0.36	0.50 0.50		0.44 0.44		V	*V _{IN} = V _{IL} or V _{IH} 24 mA I _{OL} 24 mA
I _{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0		±1.0		μA	V _I = V _{CC} , GND
V _{h(max)}	Maximum Hysteresis	4.5 5.5		1.4 1.6	1.4 1.6		1.4 1.6		V	T _A = Worst Case

*All outputs loaded; thresholds on input associated with output under test.

DC Characteristics for 'ACTQ Family Devices (Continued)

Symbol	Parameter	V _{CC} (V)	74ACTQ		54ACTQ	74ACTQ	Units	Conditions
			T _A = +25°C		T _A = −55°C to +125°C	T _A = −40°C to +85°C		
			Typ	Guaranteed Limits				
V _{h(min)}	Minimum Hysteresis	4.5 5.5		0.4 0.5	0.4 0.5	0.4 0.5	V	T _A = Worst Case
V _t ⁺	Maximum Positive Threshold	4.5 5.5		2.0 2.0	2.0 2.0	2.0 2.0	V	T _A = Worst Case
V _t [−]	Minimum Negative Threshold	4.5 5.5		0.8 0.8	0.8 0.8	0.8 0.8	V	T _A = Worst Case
I _{CCT}	Maximum I _{CC} /Input	5.5	0.6		1.6	1.5	mA	V _I = V _{CC} − 2.1V
I _{OLD}	†Minimum Dynamic Output Current	5.5			50	75	mA	V _{OLD} = 1.65V Max
I _{OHD}		5.5			−50	−75	mA	V _{OHD} = 3.85V Min
I _{CC}	Maximum Quiescent Supply Current	5.5		2.0	40.0	20.0	μA	V _{IN} = V _{CC} or GND (Note 1)
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	5.0	1.1	1.5			V	Figures 12, 13 (Notes 2, 3)
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	5.0	−0.6	−1.2			V	Figures 12, 13 (Notes 2, 3)
V _{IHD}	Minimum High Level Dynamic Input Voltage	5.0	1.9	2.2			V	(Notes 2, 4)
V _{ILD}	Maximum Low Level Dynamic Input Voltage	5.0	1.2	0.8			V	(Notes 2, 4)

†Maximum test duration 2.0 ms, one output loaded at a time.

Note 1: I_{CC} for 54ACTQ @ 25°C is identical to 74ACTQ @ 25°C.

Note 2: Plastic DIP package.

Note 3: Max number of outputs defined as (n). Data inputs are 0V to 3V. One output @ GND.

Note 4: Max number of data inputs (n) switching. (n−1) inputs switching 0V to 3V ('ACTQ). Input-under-test switching: 3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f = 1 MHz.

AC Electrical Characteristics

Symbol	Parameter	V _{CC} * (V)	74ACTQ			54ACTQ		74ACTQ		Units
			T _A = +25°C C _L = 50 pF			T _A = −55°C to +125°C C _L = 50 pF		T _A = −40°C to +85°C C _L = 50 pF		
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH}	Propagation Delay Data to Output	5.0	3.0	8.0	10.0	1.5	10.0	3.0	11.0	ns
t _{PHL}	Propagation Delay Data to Output	5.0	3.0	8.0	10.0	1.5	9.5	3.0	11.0	ns
t _{OSHL} , t _{OSLH}	Output to Output Skew**	5.0		0.5	1.0		1.0		1.0	ns

*Voltage Range 5.0 is 5.0V ± 0.5V.

**Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}). Parameter guaranteed by design.

Capacitance

Symbol	Parameter	Typ	Units	Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = OPEN
C _{PD}	Power Dissipation Capacitance	80	pF	V _{CC} = 5.0V

FACT Noise Characteristics

The setup of a noise characteristics measurement is critical to the accuracy and repeatability of the tests. The following is a brief description of the setup used to measure the noise characteristics of FACT.

Equipment:

Hewlett Packard Model 8180A Word Generator
PC-163A Test Fixture
Tektronics Model 7854 Oscilloscope

Procedure:

1. Verify Test Fixture Loading: Standard Load 50 pF, 500Ω.
2. Deskew the word generator so that no two channels have greater than 150 ps skew between them. This requires that the oscilloscope be deskewed first. Swap out the channels that have more than 150 ps of skew until all channels being used are within 150 ps. It is important to deskew the word generator channels before testing. This will ensure that the outputs switch simultaneously.
3. Terminate all inputs and outputs to ensure proper loading of the outputs and that the input levels are at the correct voltage.

4. Set V_{CC} to 5.0V.

5. Set the word generator to toggle all but one output at a frequency of 1 MHz. Greater frequencies will increase DUT heating and affect the results of the measurement.

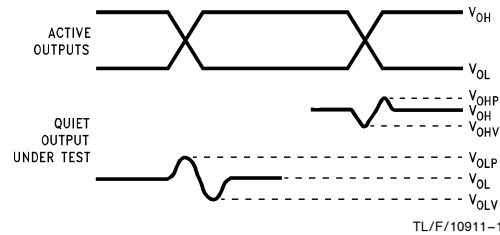


FIGURE 1. Quiet Output Noise Voltage Waveforms

Note A. V_{OHP} and V_{OLP} are measured with respect to ground reference.

Note B. Input pulses have the following characteristics: f = 1 MHz, t_r = 3 ns, t_f = 3 ns, skew < 150 ps.

6. Set the word generator input levels at 0V LOW and 3V HIGH for ACT devices and 0V LOW and 5V HIGH for AC devices. Verify levels with a digital volt meter.

FACT Noise Characteristics (Continued)

V_{OLP}/V_{OLV} and V_{OHP}/V_{OHV} :

- Determine the quiet output pin that demonstrates the greatest noise levels. The worst case pin will usually be the furthest from the ground pin. Monitor the output voltages using a 50 Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- Measure V_{OLP} and V_{OLV} on the quiet output during the HL transition. Measure V_{OHP} and V_{OHV} on the quiet output during the LH transition.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

V_{ILD} and V_{IHD} :

- Monitor one of the switching outputs using a 50 Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.

- First increase the input LOW voltage level, V_{IL} , until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input LOW voltage level at which oscillation occurs is defined as V_{ILD} .
- Next increase the input HIGH voltage level on the word generator, V_{IH} until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input HIGH voltage level at which oscillation occurs is defined as V_{IHD} .
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

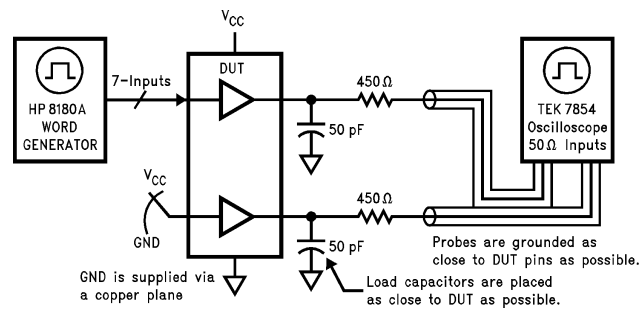


FIGURE 2. Simultaneous Switching Test Circuit

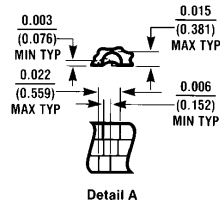
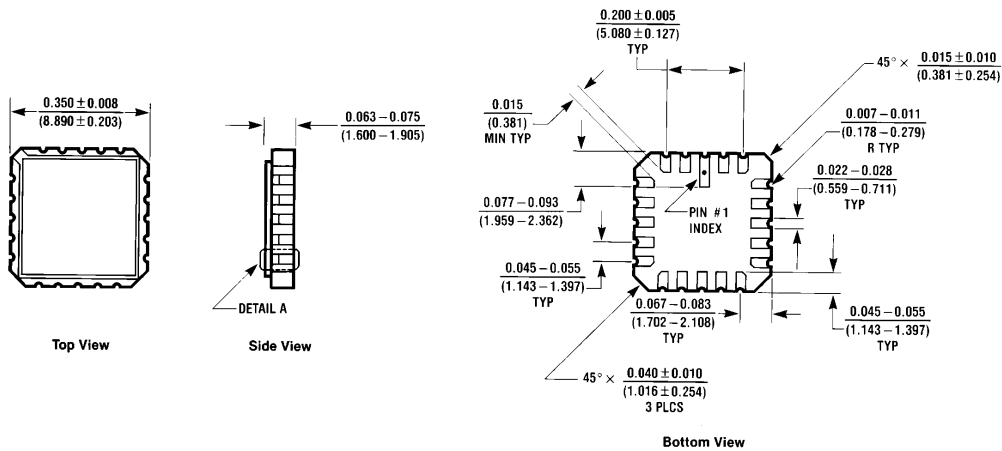
TL/F/10911-2

Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

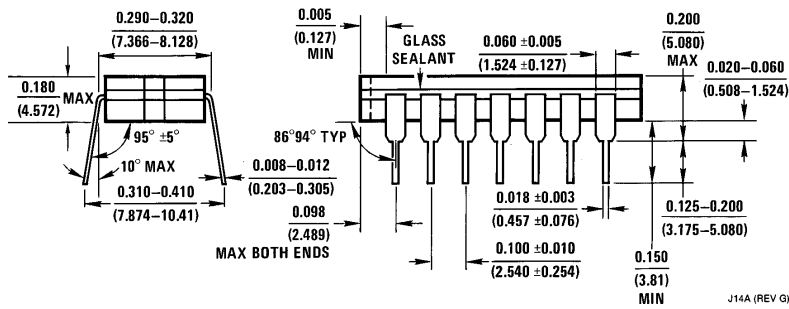
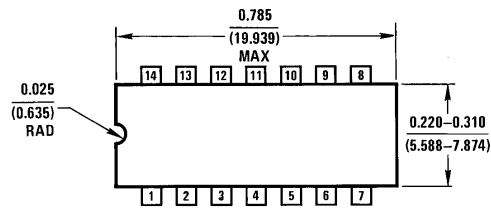
Temperature Range Family	74ACTQ	14	P	C	QR
74ACTQ = Commercial TTL—Compatible					
54ACTQ = Military TTL—Compatible					
Device Type					
Package Code					
P = Plastic DIP					
D = Ceramic DIP					
F = Flatpak					
L = Leadless Ceramic Chip Carrier (LCC)					
S = Small Outline (SOIC)					
Special Variations					
X = Devices shipped in 13" reels					
QR = Commercial grade device with burn-in					
QB = Military grade device with environmental and burn-in processing shipped in tubes					
Temperature Range					
C = Commercial (–40°C to +85°C)					
M = Military (–55°C to +125°C)					

Physical Dimensions inches (millimeters)



20-Terminal Ceramic Leadless Chip Carrier (L)
NS Package Number E20A

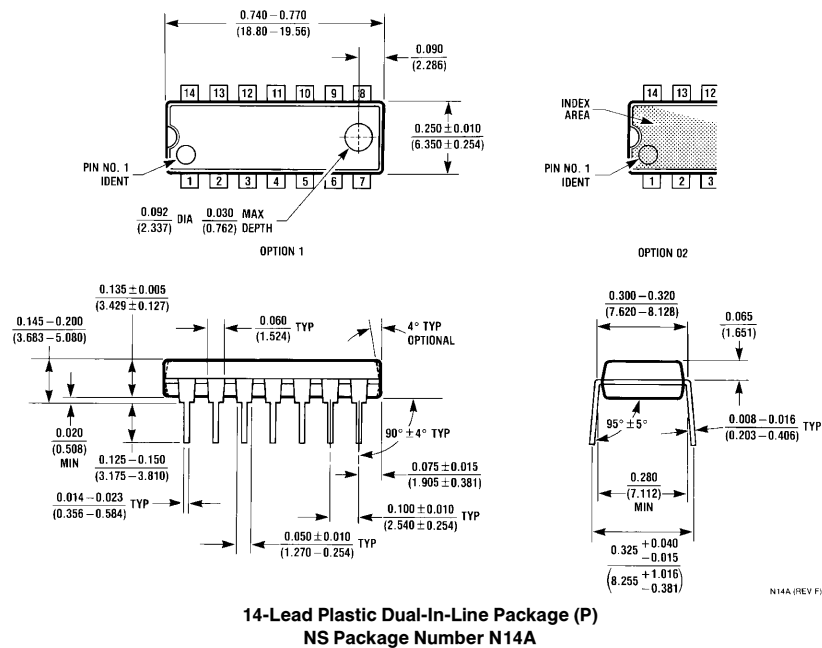
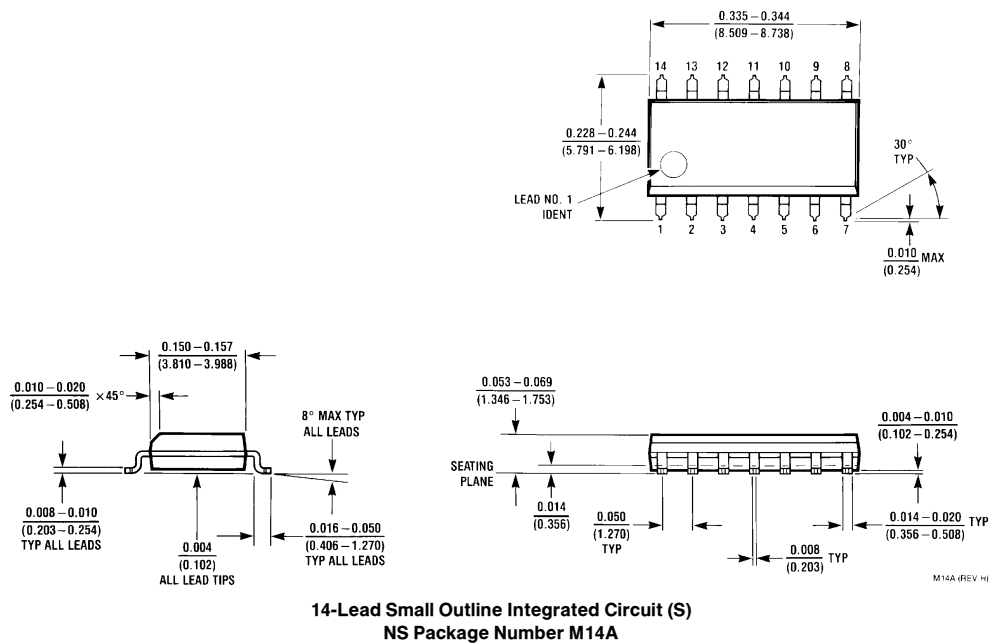
E20A (REV D)



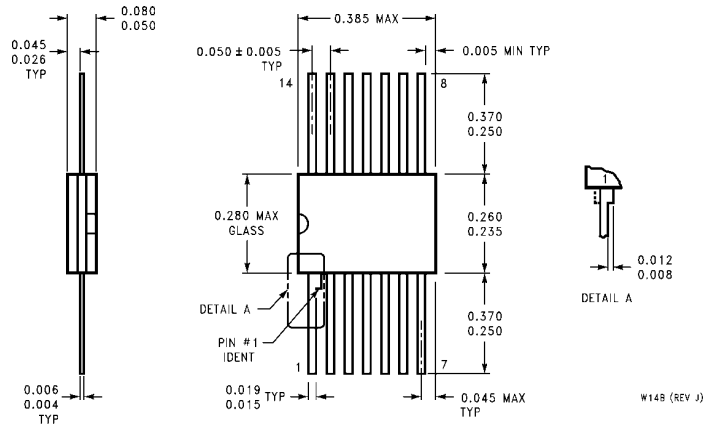
14-Lead Ceramic Dual-In-Line Package (D)
NS Package Number J14A

J14A (REV G)

Physical Dimensions inches (millimeters) (Continued)



Physical Dimensions inches (millimeters) (Continued)



14-Lead Ceramic Flatpak (F)
NS Package Number W14B

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